

## OptiMOS™2 Power-Transistor

### Features

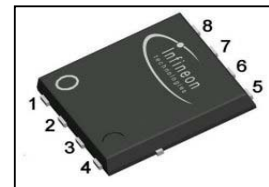
- N-channel, normal level
- Excellent gate charge x  $R_{DS(on)}$  product (FOM)
- Very low on-resistance  $R_{DS(on)}$
- 150 °C operating temperature
- Pb-free lead plating; RoHS compliant
- Qualified according to JEDEC<sup>1)</sup> for target application
- Ideal for high-frequency switching and synchronous rectification
- Halogen-free according to IEC61249-2-21



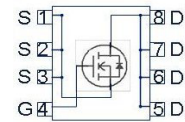
### Product Summary

|                  |      |    |
|------------------|------|----|
| $V_{DS}$         | 100  | V  |
| $R_{DS(on),max}$ | 19.6 | mΩ |
| $I_D$            | 45   | A  |

PG-TDSON-8



| Type          | Package    | Marking  |
|---------------|------------|----------|
| BSC196N10NS G | PG-TDSON-8 | 196N10NS |



**Maximum ratings**, at  $T_j=25\text{ °C}$ , unless otherwise specified

| Parameter                           | Symbol            | Conditions                                            | Value       | Unit |
|-------------------------------------|-------------------|-------------------------------------------------------|-------------|------|
| Continuous drain current            | $I_D$             | $T_C=25\text{ °C}$                                    | 45          | A    |
|                                     |                   | $T_C=100\text{ °C}$                                   | 29          |      |
|                                     |                   | $T_A=25\text{ °C}$ ,<br>$R_{thJA}=45\text{ K/W}^{2)}$ | 8.5         |      |
| Pulsed drain current <sup>3)</sup>  | $I_{D,pulse}$     | $T_C=25\text{ °C}$                                    | 164         |      |
| Avalanche energy, single pulse      | $E_{AS}$          | $I_D=45\text{ A}$ , $R_{GS}=25\text{ Ω}$              | 60          | mJ   |
| Gate source voltage                 | $V_{GS}$          |                                                       | ±20         | V    |
| Power dissipation                   | $P_{tot}$         | $T_C=25\text{ °C}$                                    | 78          | W    |
| Operating and storage temperature   | $T_j$ , $T_{stg}$ |                                                       | -55 ... 150 | °C   |
| IEC climatic category; DIN IEC 68-1 |                   |                                                       | 55/150/56   |      |

<sup>1)</sup>J-STD20 and JESD22

| Parameter | Symbol | Conditions | Values |      |      | Unit |
|-----------|--------|------------|--------|------|------|------|
|           |        |            | min.   | typ. | max. |      |

**Thermal characteristics**

|                                        |            |                                              |   |   |     |     |
|----------------------------------------|------------|----------------------------------------------|---|---|-----|-----|
| Thermal resistance, junction - case    | $R_{thJC}$ | bottom                                       | - | - | 1.6 | K/W |
|                                        |            | top                                          | - | - | 18  |     |
| Thermal resistance, junction - ambient | $R_{thJA}$ | minimal footprint                            | - | - | 62  |     |
|                                        |            | 6 cm <sup>2</sup> cooling area <sup>2)</sup> | - | - | 45  |     |

**Electrical characteristics**, at  $T_j=25\text{ }^{\circ}\text{C}$ , unless otherwise specified

**Static characteristics**

|                                  |               |                                                                                 |     |      |      |               |
|----------------------------------|---------------|---------------------------------------------------------------------------------|-----|------|------|---------------|
| Drain-source breakdown voltage   | $V_{(BR)DSS}$ | $V_{GS}=0\text{ V}$ , $I_D=1\text{ mA}$                                         | 100 | -    | -    | V             |
| Gate threshold voltage           | $V_{GS(th)}$  | $V_{DS}=V_{GS}$ , $I_D=42\text{ }\mu\text{A}$                                   | 2   | 3    | 4    |               |
| Zero gate voltage drain current  | $I_{DSS}$     | $V_{DS}=100\text{ V}$ , $V_{GS}=0\text{ V}$ , $T_j=25\text{ }^{\circ}\text{C}$  | -   | 0.01 | 1    | $\mu\text{A}$ |
|                                  |               | $V_{DS}=100\text{ V}$ , $V_{GS}=0\text{ V}$ , $T_j=125\text{ }^{\circ}\text{C}$ | -   | 10   | 100  |               |
| Gate-source leakage current      | $I_{GSS}$     | $V_{GS}=20\text{ V}$ , $V_{DS}=0\text{ V}$                                      | -   | 1    | 100  | nA            |
| Drain-source on-state resistance | $R_{DS(on)}$  | $V_{GS}=10\text{ V}$ , $I_D=45\text{ A}$                                        | -   | 16.7 | 19.6 | m $\Omega$    |
| Gate resistance                  | $R_G$         |                                                                                 | -   | 1    | -    | $\Omega$      |
| Transconductance                 | $g_{fs}$      | $ V_{DS} >2 I_D R_{DS(on)max}$ , $I_D=45\text{ A}$                              | 24  | 48   | -    | S             |

<sup>2)</sup> Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm<sup>2</sup> (one layer, 70  $\mu\text{m}$  thick) copper area for drain connection. PCB is vertical in still air.

<sup>3)</sup> see figure 3

| Parameter | Symbol | Conditions | Values |      |      | Unit |
|-----------|--------|------------|--------|------|------|------|
|           |        |            | min.   | typ. | max. |      |

**Dynamic characteristics**

|                              |              |                                                                                 |   |      |      |    |
|------------------------------|--------------|---------------------------------------------------------------------------------|---|------|------|----|
| Input capacitance            | $C_{iss}$    | $V_{GS}=0\text{ V}, V_{DS}=50\text{ V},$<br>$f=1\text{ MHz}$                    | - | 1700 | 2300 | pF |
| Output capacitance           | $C_{oss}$    |                                                                                 | - | 250  | 330  |    |
| Reverse transfer capacitance | $C_{rss}$    |                                                                                 | - | 17   | 26   |    |
| Turn-on delay time           | $t_{d(on)}$  | $V_{DD}=50\text{ V}, V_{GS}=10\text{ V},$<br>$I_D=25\text{ A}, R_G=1.6\ \Omega$ | - | 16   | 24   | ns |
| Rise time                    | $t_r$        |                                                                                 | - | 22   | 33   |    |
| Turn-off delay time          | $t_{d(off)}$ |                                                                                 | - | 18   | 28   |    |
| Fall time                    | $t_f$        |                                                                                 | - | 5    | 8    |    |

**Gate Charge Characteristics<sup>4)</sup>**

|                       |               |                                                                            |   |     |    |    |
|-----------------------|---------------|----------------------------------------------------------------------------|---|-----|----|----|
| Gate to source charge | $Q_{gs}$      | $V_{DD}=50\text{ V}, I_D=25\text{ A},$<br>$V_{GS}=0\text{ to }10\text{ V}$ | - | 9   | 12 | nC |
| Gate to drain charge  | $Q_{gd}$      |                                                                            | - | 6   | 9  |    |
| Switching charge      | $Q_{sw}$      |                                                                            | - | 10  | 14 |    |
| Gate charge total     | $Q_g$         |                                                                            | - | 25  | 34 |    |
| Gate plateau voltage  | $V_{plateau}$ |                                                                            | - | 5.2 | -  | V  |
| Output charge         | $Q_{oss}$     | $V_{DD}=50\text{ V}, V_{GS}=0\text{ V}$                                    | - | 27  | 35 | nC |

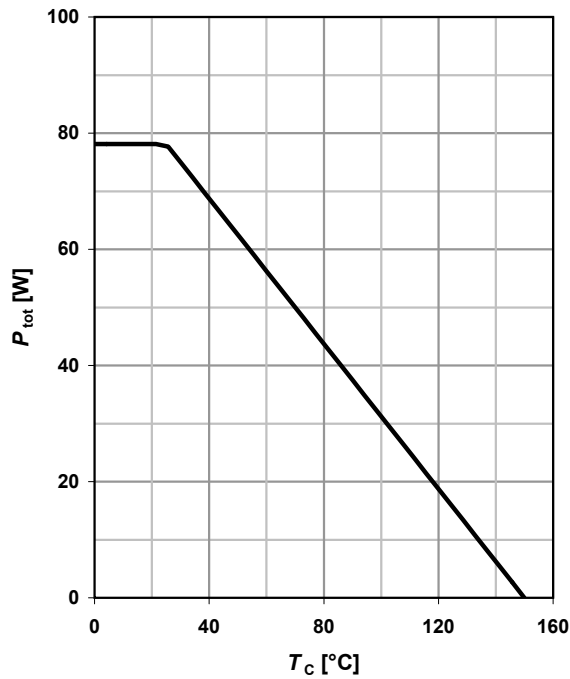
**Reverse Diode**

|                                  |               |                                                                           |   |     |     |    |
|----------------------------------|---------------|---------------------------------------------------------------------------|---|-----|-----|----|
| Diode continuous forward current | $I_S$         | $T_C=25\text{ °C}$                                                        | - | -   | 45  | A  |
| Diode pulse current              | $I_{S,pulse}$ |                                                                           | - | -   | 180 |    |
| Diode forward voltage            | $V_{SD}$      | $V_{GS}=0\text{ V}, I_F=45\text{ A},$<br>$T_j=25\text{ °C}$               | - | 1.0 | 1.3 | V  |
| Reverse recovery time            | $t_{rr}$      | $V_R=50\text{ V}, I_F=25\text{ A},$<br>$di_F/dt=100\text{ A}/\mu\text{s}$ | - | 82  | -   | ns |
| Reverse recovery charge          | $Q_{rr}$      |                                                                           | - | 199 | -   | nC |

<sup>4)</sup> See figure 16 for gate charge parameter definition

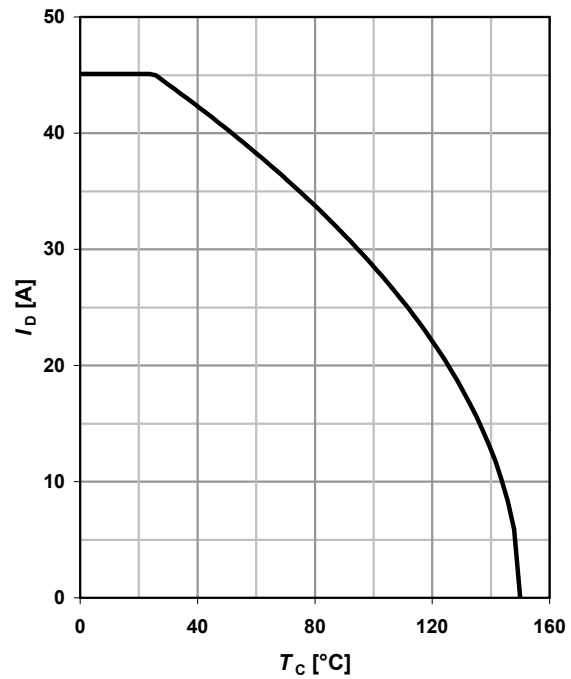
### 1 Power dissipation

$$P_{\text{tot}} = f(T_C)$$



### 2 Drain current

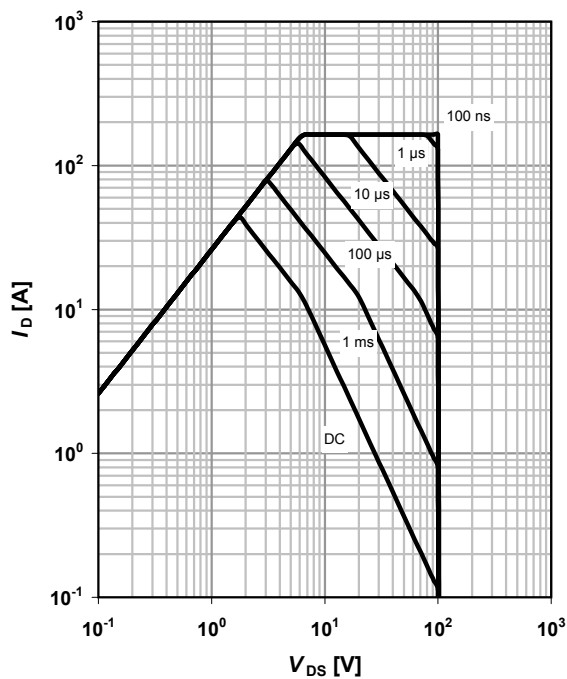
$$I_D = f(T_C); V_{GS} \geq 10 \text{ V}$$



### 3 Safe operating area

$$I_D = f(V_{DS}); T_C = 25^\circ\text{C}; D = 0$$

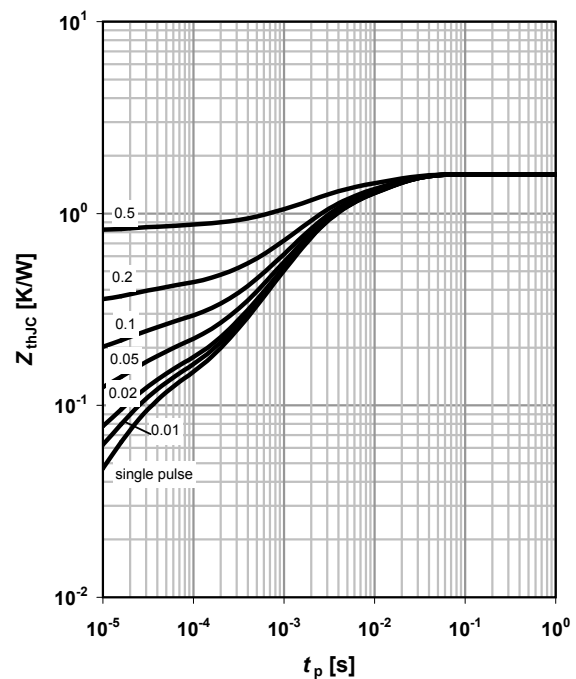
parameter:  $t_p$



### 4 Max. transient thermal impedance

$$Z_{\text{thJC}} = f(t_p)$$

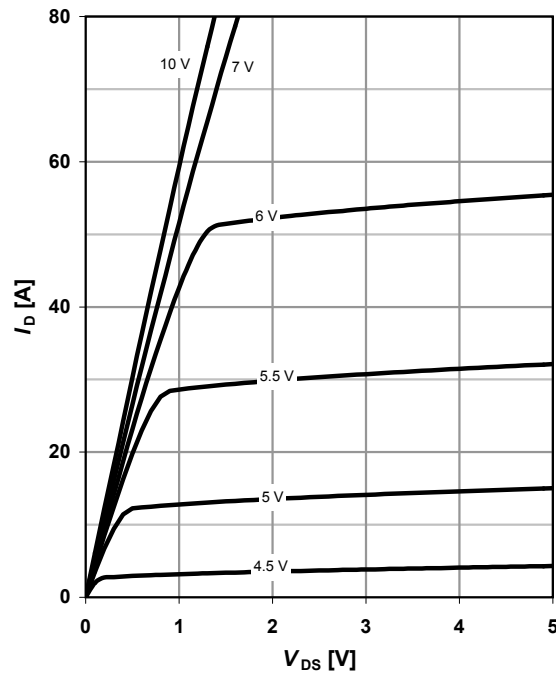
parameter:  $D = t_p / T$



### 5 Typ. output characteristics

$$I_D = f(V_{DS}); T_j = 25^\circ\text{C}$$

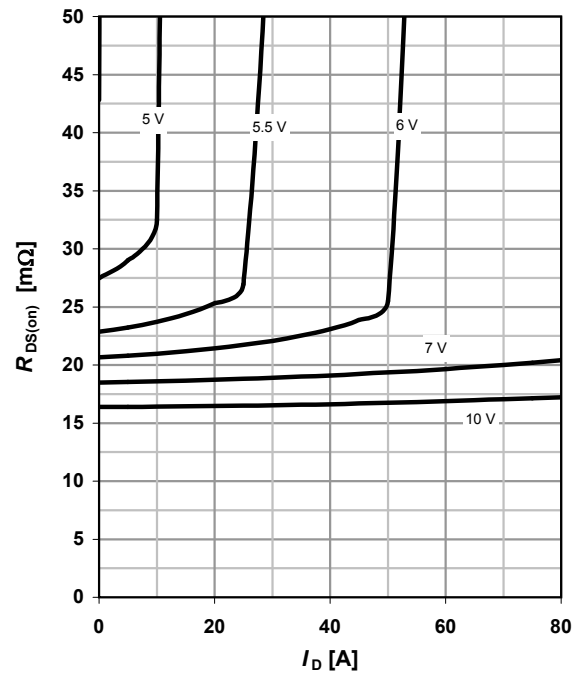
parameter:  $V_{GS}$



### 6 Typ. drain-source on resistance

$$R_{DS(on)} = f(I_D); T_j = 25^\circ\text{C}$$

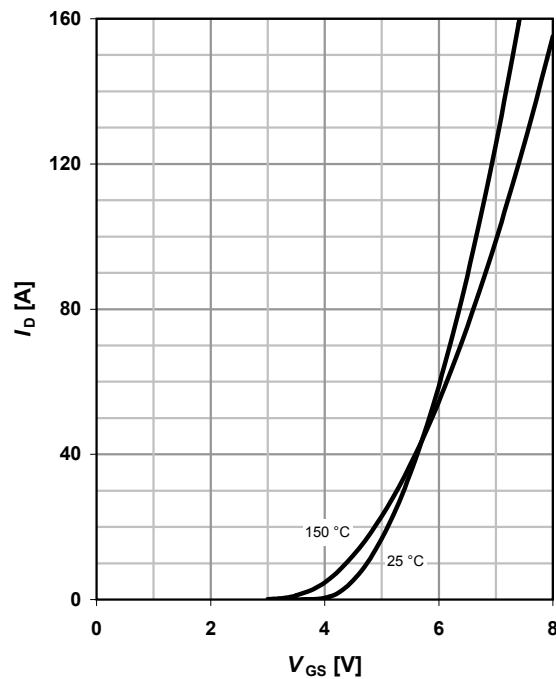
parameter:  $V_{GS}$



### 7 Typ. transfer characteristics

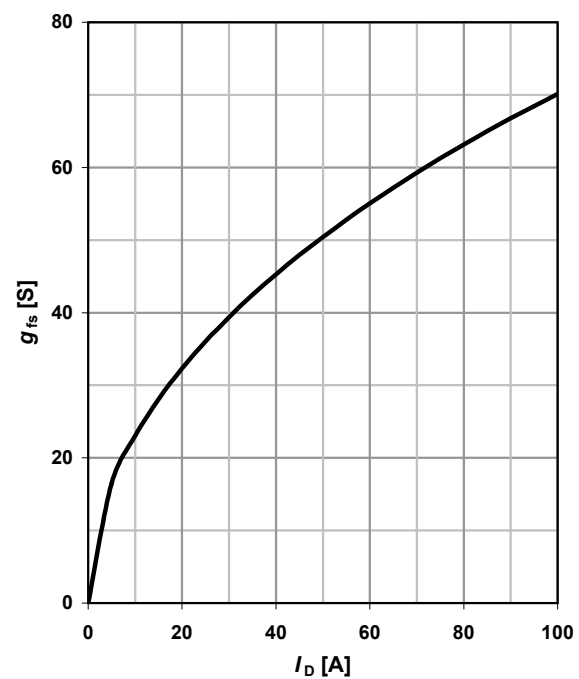
$$I_D = f(V_{GS}); |V_{DS}| > 2|I_D|R_{DS(on)max}$$

parameter:  $T_j$



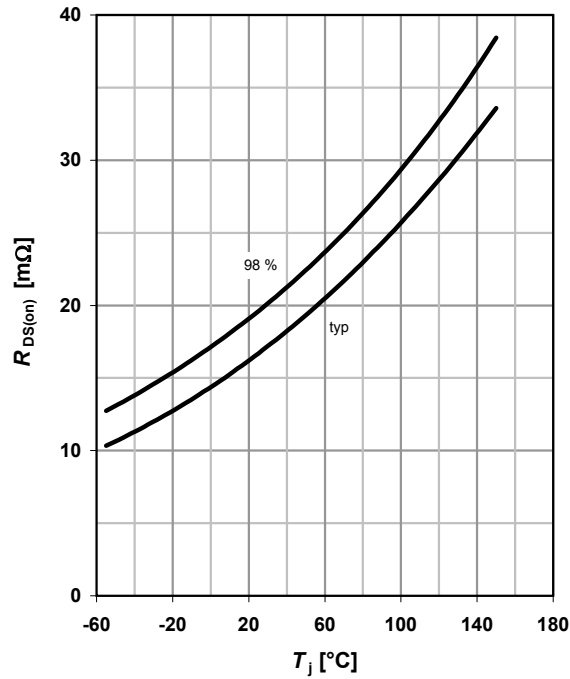
### 8 Typ. forward transconductance

$$g_{fs} = f(I_D); T_j = 25^\circ\text{C}$$



### 9 Drain-source on-state resistance

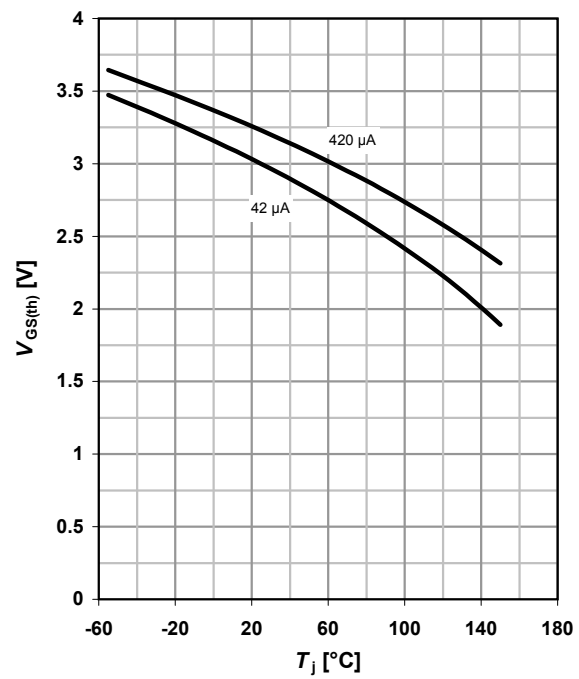
$$R_{DS(on)} = f(T_j); I_D = 45 \text{ A}; V_{GS} = 10 \text{ V}$$



### 10 Typ. gate threshold voltage

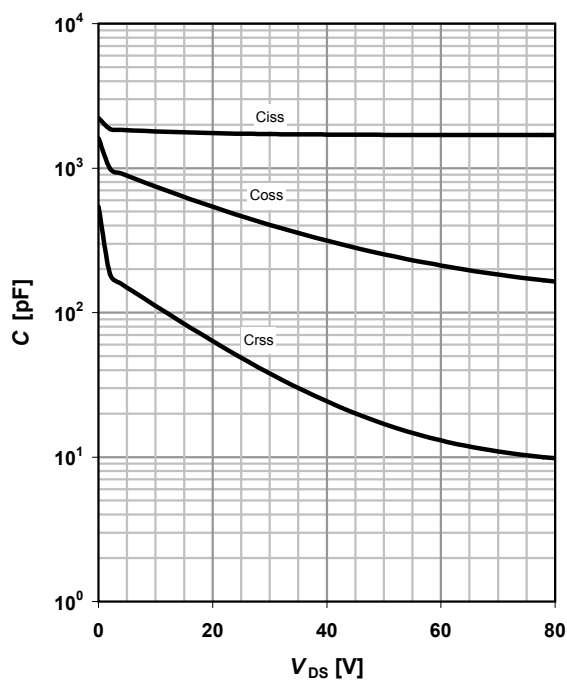
$$V_{GS(th)} = f(T_j); V_{GS} = V_{DS}$$

parameter:  $I_D$



### 11 Typ. capacitances

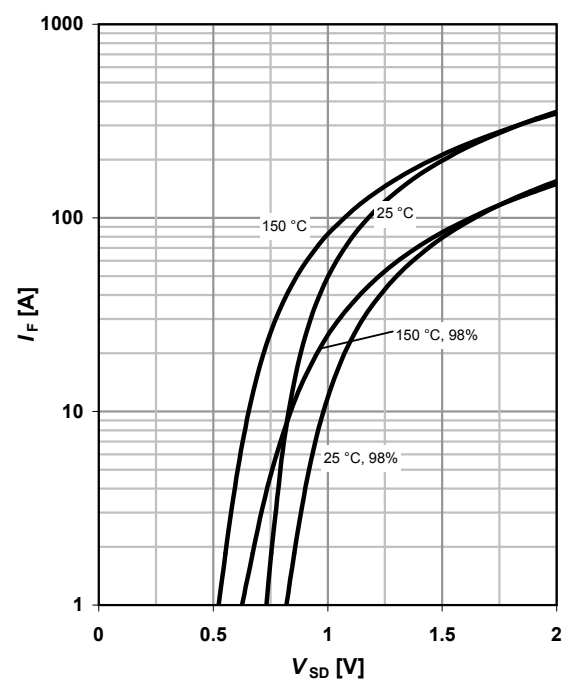
$$C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$$



### 12 Forward characteristics of reverse diode

$$I_F = f(V_{SD})$$

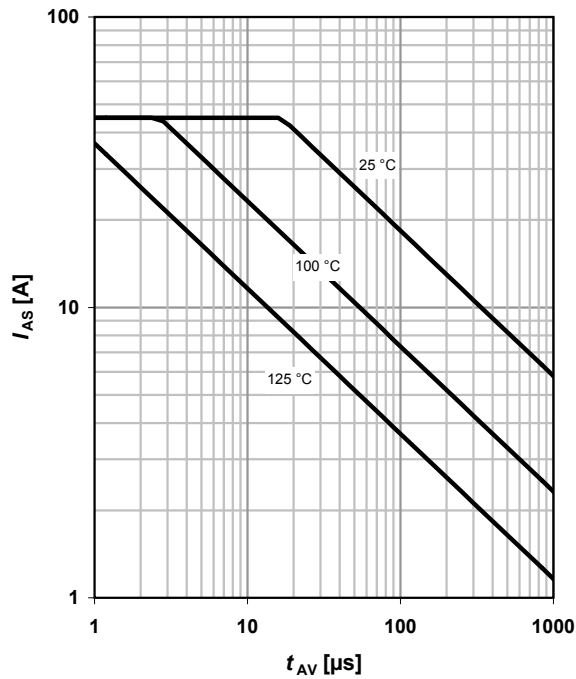
parameter:  $T_j$



### 13 Avalanche characteristics

$$I_{AS} = f(t_{AV}); R_{GS} = 25 \Omega$$

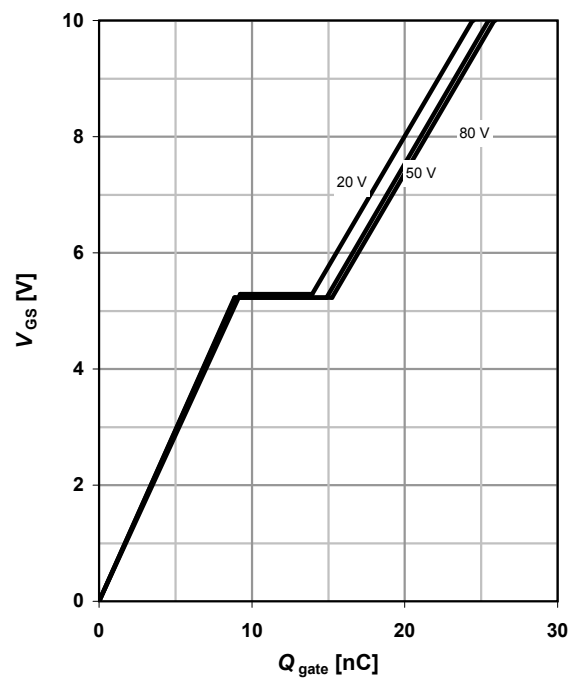
parameter:  $T_{j(\text{start})}$



### 14 Typ. gate charge

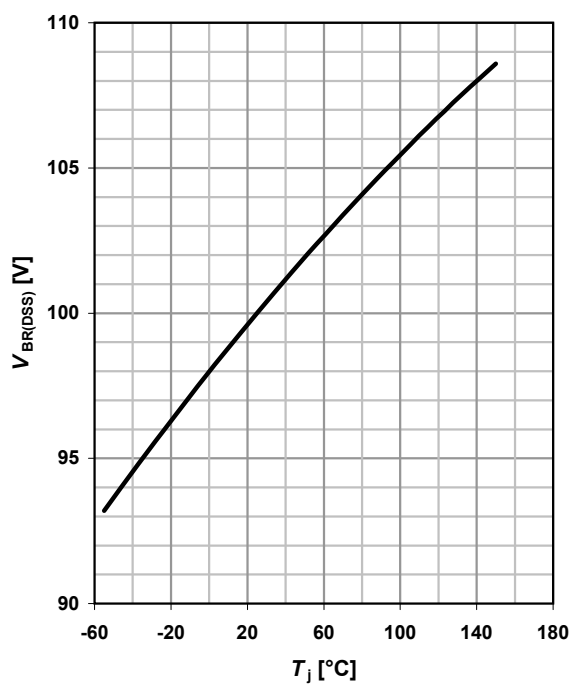
$$V_{GS} = f(Q_{\text{gate}}); I_D = 25 \text{ A pulsed}$$

parameter:  $V_{DD}$



### 15 Drain-source breakdown voltage

$$V_{BR(DSS)} = f(T_j); I_D = 1 \text{ mA}$$

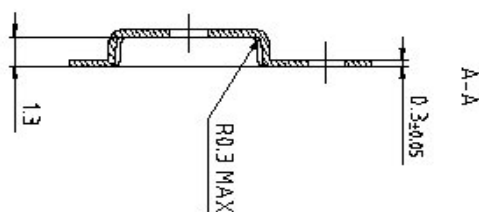


### 16 Gate charge waveforms



| DIM  | MILLIMETERS |       | INCHES |       |
|------|-------------|-------|--------|-------|
|      | MIN         | MAX   | MIN    | MAX   |
| A    | 0.90        | 1.10  | 0.035  | 0.043 |
| b    | 0.34        | 0.54  | 0.013  | 0.021 |
| b1   | 0.02        | 0.22  | 0.001  | 0.008 |
| c    | 0.15        | 0.35  | 0.006  | 0.014 |
| D=D1 | 4.95        | 5.35  | 0.195  | 0.211 |
| D2   | 4.20        | 4.40  | 0.165  | 0.173 |
| E    | 5.95        | 6.35  | 0.234  | 0.250 |
| E1   | 5.70        | 6.10  | 0.224  | 0.240 |
| E2   | 3.40        | 3.80  | 0.134  | 0.150 |
| e    | 1.27        |       | 0.050  |       |
| N    | 8           |       | 8      |       |
| L    | 0.45        | 0.65  | 0.018  | 0.026 |
| □    | 8.5°        | 11.5° | 8.5°   | 11.5° |
| aaa  | 0.25        |       | 0.010  |       |
| eee  | 0.05        |       | 0.002  |       |
| F1   | 6.75        | 6.95  | 0.266  | 0.274 |
| F2   | 4.60        | 4.80  | 0.181  | 0.189 |
| F3   | 4.36        | 4.56  | 0.172  | 0.180 |
| F4   | 0.55        | 0.75  | 0.022  | 0.030 |
| F5   | 0.52        | 0.72  | 0.020  | 0.028 |
| F6   | 1.10        | 1.30  | 0.043  | 0.051 |
| F7   | 0.40        | 0.60  | 0.016  | 0.024 |
| F8   | 0.60        | 0.80  | 0.024  | 0.031 |
| F9   | 0.53        | 0.73  | 0.021  | 0.029 |
| F10  | 4.90        | 5.10  | 0.193  | 0.201 |
| F11  | 0.53        | 0.73  | 0.021  | 0.029 |

|                                            |  |
|--------------------------------------------|--|
| <p><b>DOCUMENT NO.</b><br/>Z8B00003332</p> |  |
| <p><b>SCALE</b></p>                        |  |
| <p><b>EUROPEAN PROJECTION</b></p>          |  |
| <p><b>ISSUE DATE</b><br/>08-03-2007</p>    |  |
| <p><b>REVISION</b><br/>03</p>              |  |



2009-11-04

**Published by**  
**Infineon Technologies AG**  
**81726 Munich, Germany**  
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